

Citations for Ion : Pb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1956	Jesse, W. P. Saduakis, J. 'Recoil Particles from Po210 and Their Ionization in Argon and Helium' <i>Phys. Rev., 102, 389-90 (1956)</i> <i>Comment : R. 103 keV 206Pb -> He, Ar</i>	1956-Jess
1963	Zahn, P. 'Energieverlust von Alpha-Rückstosskernen in Formvar' <i>Z. Physik, 175, 85-98 (1963)</i> <i>Comment : S. 169 keV 208Pb -> Formvar</i>	1963-Zahn
1964	Sidenius, G. 'Measurement of dE/dX in Gases with Low Energy Heavy Particles' <i>M. R. C. McDowell (Ed.) Atomic Collision Processes, North-Holland, Amsterdam, P. 709-16 (1964)</i> <i>Comment : S. (20-50 keV) Cl, Ga, Zr, Sb, Pb, Fe, Ca, Ge, U -> H2</i>	1964-Side
1965	Cano, G. L. Dressel, R. W. 'Energy Loss and Resultant Charge of Recoil Particles from Alpha Disintegration in Surface Deposits of 210Po and 241Am' <i>Phys. Rev A., 139, 1883-92 (1965).</i> <i>Comment : R. 103 keV 206Pb, 924 keV 239Np -> Ar</i>	1965-Cano
1966	Marx, D. 'Messung Des Bremsvermögens von Pb208 - Alpha - Rückstoss-Kernen in Fester Materie' <i>Z. Physik, 195, 26-43 (1966)</i> <i>Comment : S. 169 keV 208Pb -> C, Ag, Au</i>	1966-Marx
1968	Cano, G. L. 'Total Ionization and Range of Low-Energy Recoil Particles in Pure and Binary Gases' <i>Phys. Rev., 169, 277-79 (1968)</i> <i>Comment : R. 103 keV 206Pb -> Ne, Ar, Xe, N2, Air, Hydrocarbons</i>	1968-Cano
1968	Ibel, K. Sizmann, R. 'Energy Loss of <110> Channeled Alpha-Recoil Atoms in Gold' <i>Phys. Stat. Sol., 29, 403-15 (1968)</i> <i>Comment : S. 169 keV 208Pb, 146 keV 210Pb, 116 keV 208Tl -> Au (Cryst.)</i>	1968-Ibel
1968	Poole, D. H. Warner, A. G. Hancock, R. Woodley, R. L. 'Stopping Cross-Section Measurements in Carbon using Recoil from Radioactive Decay' <i>Brit. J. Appl. Phys., 1, 309-12 (1968)</i> <i>Comment : S, dS. 169 keV Pb -> C</i>	1968-Pool
1969	Hancock, R. Warner, R. G. Woolley, R. L. 'Collision Cascades in Gold in the Energy Range 3-169 keV' <i>J. Phys. D: Appl. Phys., 2, 991-98 (1969)</i> <i>Comment : S. 169 keV Pb -> Au</i>	1969-Hanc

Citations for Ion : Pb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1974	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N.Y., P. 235-44 (1974)</i> <i>Comment : R, dR, dR(Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si</i>	1974-Gran
1975	Hvelplund, P. 'Energy Loss and Straggling of 100-500 keV 90Th, 82Pb, 80Hg, and 64Gd in H2' <i>Phys. Rev. A, 11, 1921-27 (1975)</i> <i>Comment : S, dS. 100-500 keV Gd, Hg, Pb, Th -> H2</i>	1975-Hvel
1975	Martini, V. 'Energy-Loss Measurements of keV-Ions in Gases by Time-Of-Flight Spectroscopy' <i>Nucl. Inst. Methods, 124, 119-24 (1975)</i> <i>Comment : S. 25-75 keV Pb -> He</i>	1975-Mart
1975	Williams, J. S. Grant, W. A. 'High Resolution Rutherford Backscattering and Its Application to Ion Range and Ion Collectionrad' <i>Rad. Effects, 25, 55-56 (1975)</i> <i>Comment : R, dR. 20-80 keV Kr, Xe, Cs, Dy, Au, Pb, Bi -> Si, Al</i>	1975-Will
1976	Grant, W. A. Dodds, D. Williams, J. S. Christodoulides, C. E. Baragiola, R. A. 'Heavy Ion Ranges in Silicon and Aluminum' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 693-703 (1976)</i> <i>Comment : R. 0.01 < Epsilon < 0.8 Cr, Ni, Ga, As, Br, Mo, Cs, La, Nd, Dy, Ta, Pt, Au, Pb -> Si, Al</i>	1976-Gran
1976	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering' <i>O. Meyer, G. Linker, F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N.Y., 457-69 (1976)</i> <i>Comment : R, dR, dR (Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si</i>	1976-Gran2
1976	Grant, W. A. Williams, J. S. Dodds, D. 'Measurement of the Lateral Spread of Heavy Ions Implanted into Silicon' <i>Rad. Effects, 29, 189-90 (1976)</i> <i>Comment : dR(Lateral). (10-40 keV) Cu, Cd, Xe, Dy, Kr, W, Pb, Bi -> Si</i>	1976-Gran3
1976	Martini, V. 'Stopping Cross Section Measurements with Heavy Ions in the keV Range in Gases by Time-Of-Flight Spectroscopy' <i>Nucl. Inst. Methods, 139, 163-167 (1976).</i> <i>Comment : S. 20-156 keV Pb -> H2</i>	1976-Mart

Citations for Ion : Pb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
	Williams, J. S.	1976-Will
1976	'The Application of Low Angle Rutherford Backscattering to Surface Layer Analysis' <i>Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N.Y., P. 223-34 (1976)</i> <i>Comment : R, dR. 5 keV Cr -> Ge, 20 keV Pb -> Si</i>	
1977	Christodoulides, C. E. Grant, W. A. Williams, J. S. 'Rutherford Backscattering Analysis of Ion-Implanted, Thermally Oxidized Silicon' <i>J. Electrochem. Soc., 124, 1651-1653 (1977)</i> <i>Comment : R. 20 keV Dy, Pb, Xe -> Si (With SiO₂)</i>	1977-Chri
1977	Christodoulides, C. E. Grant, W. A. Williams, J. S. 'Lattice Location of Lead Implanted into Silicon at Room Temperature' <i>Appl. Phys., 13, 391-393 (1977)</i> <i>Comment : R, dR. 20 keV Pb -> Si [111]</i>	1977-Chri2
1978	Campisano, S. U. Ciavola, G. Vitali, G. 'Channeling and Rheed Analyses of Pb-Implantation in Silicon' <i>Appl. Phys., 15, 233-237 (1978)</i> <i>Comment : R. 40 keV Pb -> Si</i>	1978-Camp
1978	Christodoulides, C. E. 'Impurity Redistribution in Pb Implanted and Annealed Silicon' <i>Phys. Letters, 67A, 83-86 (1978)</i> <i>Comment : R, dR. 80-180 keV Pb -> Si</i>	1978-Chri
1978	Christodoulides, C. E. Carter, G. Williams, J. S. 'Implant Redistribution in High-Dose Ion Implanted and Annealed Silicon' <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -a (1978)</i> <i>Comment : R, dR. 20-80 keV As, Pb -> Si</i>	1978-Chri2
1978	Combasson, J. L. Farmery, B. W. McCulloch, D. Neilson, G. W. Thompson, M. W. 'Heavy Ion Ranges in Aluminum and Silicon' <i>Rad. Effects, 36, 149-156 (1978)</i> <i>Comment : R, dR. 20-250 keV Cs, La, Pr, Eu, Tb, Dy, Ho, Er, Lu, Hf, Pt, Au, Tl, Pb, Bi -> Al; Sm, Eu, Gd, Tb, Dy -> Si</i>	1978-Comb
1978	Palmetshofer, L. Vierlinger, E. Heinrich, H. Haas, L. D. 'Evaluation of Doping Profiles in Ion-Implanted PbTe' <i>J. Appl. Phys., 49, 1128-1130 (1978)</i> <i>Comment : R, dR. 300 keV Pb -> PbTe</i>	1978-Palm3
1978	Pape, H. Clere, H. G. Schmidt, K. H. 'Energy Loss of Heavy Ions in Carbon Foils' <i>Z. Physik A, 286, 159-162 (1978).</i> <i>Comment : S. 0.2-1.4 MeV Ar, Ti, Kr, Xe, Pb, U -> C</i>	1978-Pape

Citations for Ion : Pb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)</i> <i>Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si</i>	1979-Sant
1980	Besenbacher, F. Bottiger, J. Laursen, T. Loftager, P. Moller, W. 'Z1-Oscillations in Low-Energy Heavy-Ion Ranges' <i>Nucl. Inst. Methods, 170, 183-188 (1980)</i> <i>Comment : R, dR. Atomic Numbers 18-92 (epsilon=.015) -> Si</i>	1980-Bese2
1980	Bimbot, R. Gardes, D. Geissel, H. Kitahara, T. Armbuster, P. 'Stopping Power Measurements for 3-5 MeV/amu Kr, Xe, Pb and U in Solids' <i>Nucl. Inst. Methods, 174, 231-236 (1980)</i> <i>Comment : S. Kr, Xe, Pb, U (3-5 MeV/amu) -> C, Al, Ti, Ni, Zr, Ag, Ta, Ir, Au, Mylar, Hostaphan</i>	1980-Bimb
1980	Bister, M. Keinonen, J. Anttila, A. 'On Dissimilarities of Heavy Ion Ranges in Aluminum and Silicon' <i>Phys. Letters, A, (1980)</i> <i>Comment : R, dR. 120 keV Pb -> Al, Si</i>	1980-Bist
1980	Christodoulides, C. E. Carter, G. Williams, J. S. 'Implant Redistribution in High-Dose Ion Implanted and Annealed Silicon' <i>Rad. Effects, 48, 87-90 (1980)</i> <i>Comment : R, dR. 80 keV Pb -> Si</i>	1980-Chri
1982	Geissel, H. Laichter, Yl Schneider, W. F. W. Armbruster, P. 'Energy Loss and Energy Loss Straggling of Fast Heavy Ions in Matter' <i>Nucl. Inst. Methods, 194, 21-29 (1982)</i> <i>Comment : S. Heavy Ions (18 - 92) at 0.5-10 MeV/amu -> 17 Solids and 5 Gases</i>	1982-Geis
1983	Geissel, H. Laichter, Y. Schneider, W. F. W. Armbruster, P. 'On the Effective Charges from Stopping Powers of 0.5-10 MeV/amu Heavy Ions' <i>Phys. Letters, 99A, no. 2-3, 77-80 (1983)</i> <i>Comment : S. Kr, Xe, W, Pb, U (1-6 MeV/amu) -> 13 metallic foils</i>	1983-Geis
1986	Izsak, K. Berthold, J. Kalbitzer, S. 'Range Phenomena of Low Energy Ions in Solids' <i>Nucl. Inst. Methods, B15, 34-41 (1986)</i> <i>Comment : R. In, Xe, Pb, Cs, Au, (.01 < epsilon < 1) -> Al, Si, Ni, Ri, Ge, Al2O3</i>	1986-Izsa
1988	Geissel, H. Laichter, Y. Schneider, W. F. W. Armbruster, P. 'Observation of a Gas-Solid Difference in the Stopping Powers of 1-10 MeV/amu Heavy Ions' <i>Phys. Letters, 88A, 26 (1988)</i> <i>Comment : S. Kr, Xe, Pb, U (1-10 MeV/amu) -> Ti, Ar, Zr, Kr. Gas/Solid stopping differences.</i>	1988-Geis

Citations for Ion : Pb

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1988	Grande, P. L. Fichtner, P. F. P. Behar, M. Zawislak, F. C. 'Range Parameters of Heavy Ions Implanted into C Films' <i>Nucl. Inst. Methods, B33, 122-124 (1988)</i> Comment : R, dR . Pb, Yb, Er, Cu (10-200 keV) -> C	1988-Gran2
1996	Bimbot, R. Barbey, S. Benfoughal, T. Clapier, F. Mirea, M. 'Stopping Powers of Gases for Very Heavy Ions' <i>Nucl. Inst. Methods, B107, 9-14 (1996)</i> Comment : S. U, Pb (24 MeV/amu, 29 MeV/amu) -> H, N, O, N, Ar, Kr, Xe	1996-Bimb
2000	Weick, H. Geissel, H. Scheidenberger, C. Attallah, F. Cortina, D. 'Drastic Enhancement of Energy-Loss Straggling of Relativistic Heavy Ions due to Charge-State Fluctuations' <i>Phys. Rev. Lett., 85, 2725-2728 (2000)</i> Comment : dS. Au, Pb, Bi (100 - 1000 MeV/u) -> Be, Ag, Au, Ta, Pb, Al, Bi, Cu,	2000-Weic
2000	Weick, H. Geissel, H. Scheidenberger, C. Attallah, F. Baumann, T. 'Slowing Down of Relativistic Few-Electron Heavy Ions' <i>Nucl. Inst. Methods, B164-165, 168-179 (2000)</i> Comment : S. Au, Pb, Bi (100 - 1000 MeV/u) -> Be, Al, Cu, Ag, Ta, Au, Pb	2000-Weic2